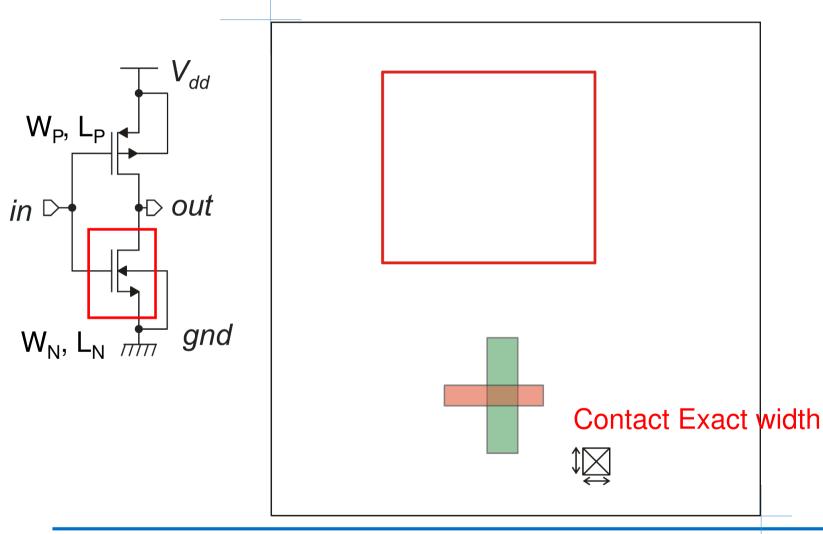
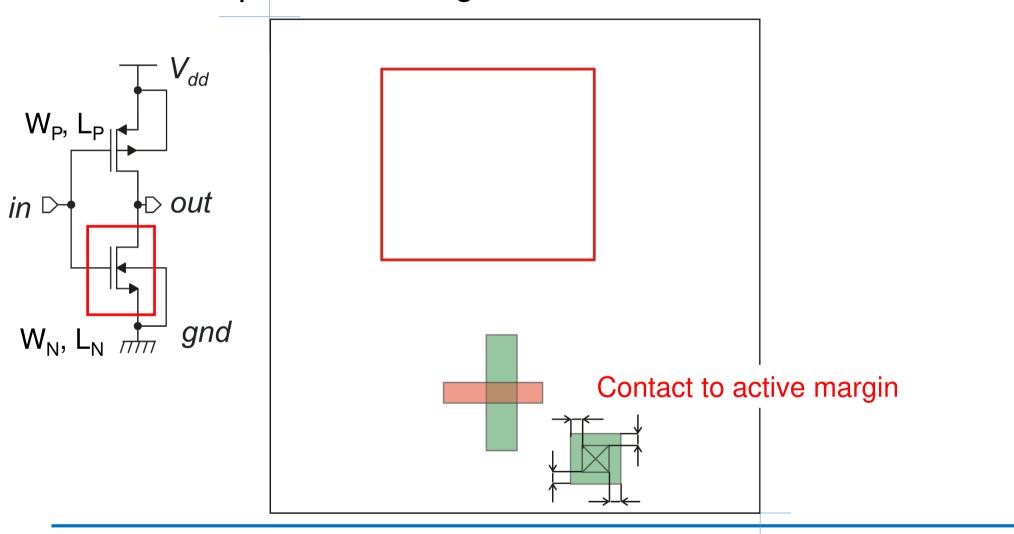


P. Bruschi – Microelectronic System Design

Let's introduce a contact

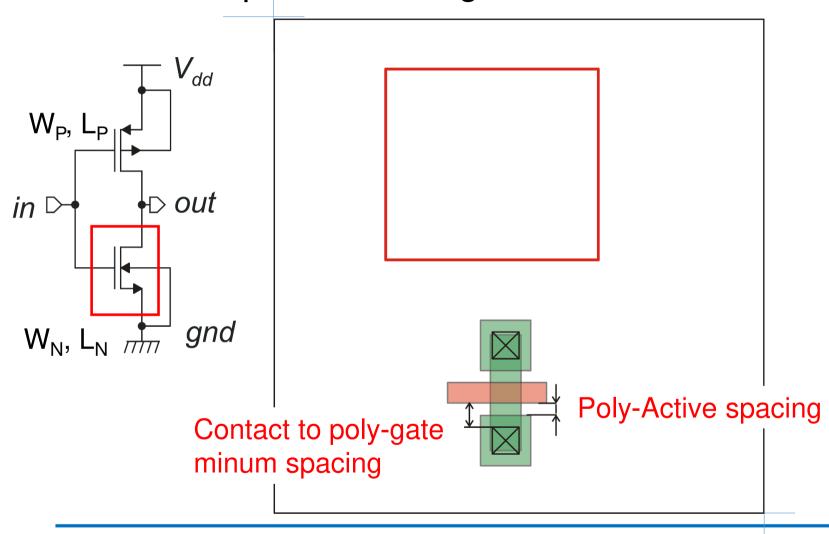


Then, we provide enough active surround to the contact

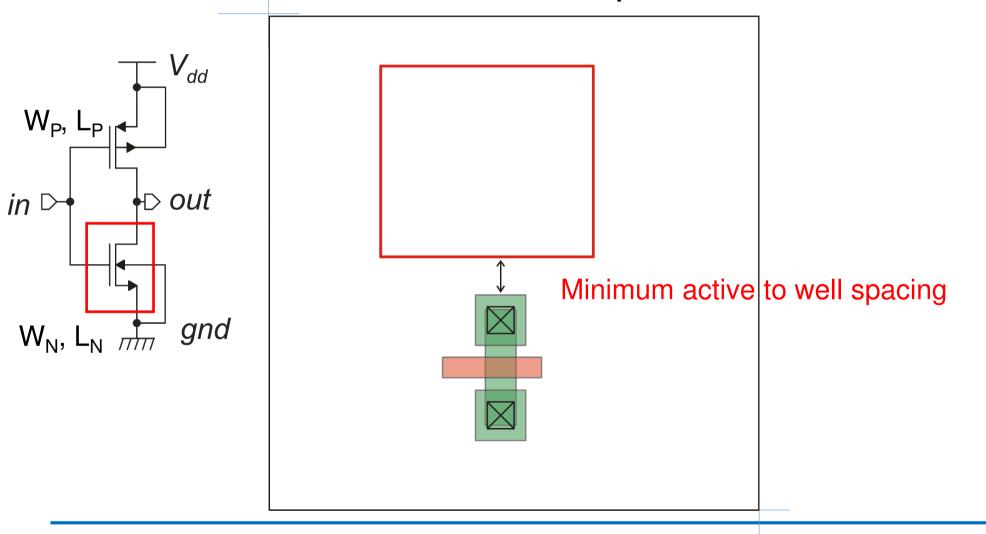


P. Bruschi – Microelectronic System Design

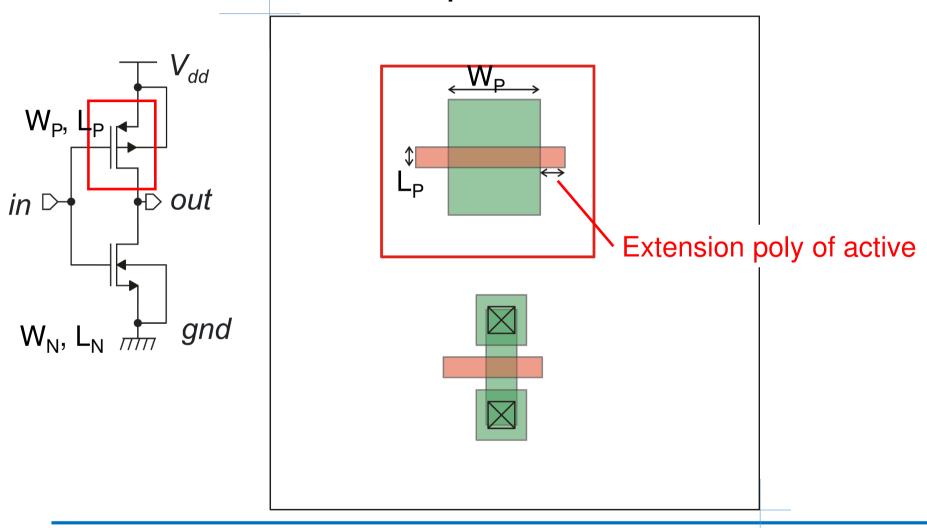
Then, we provide enough active surround to the contact



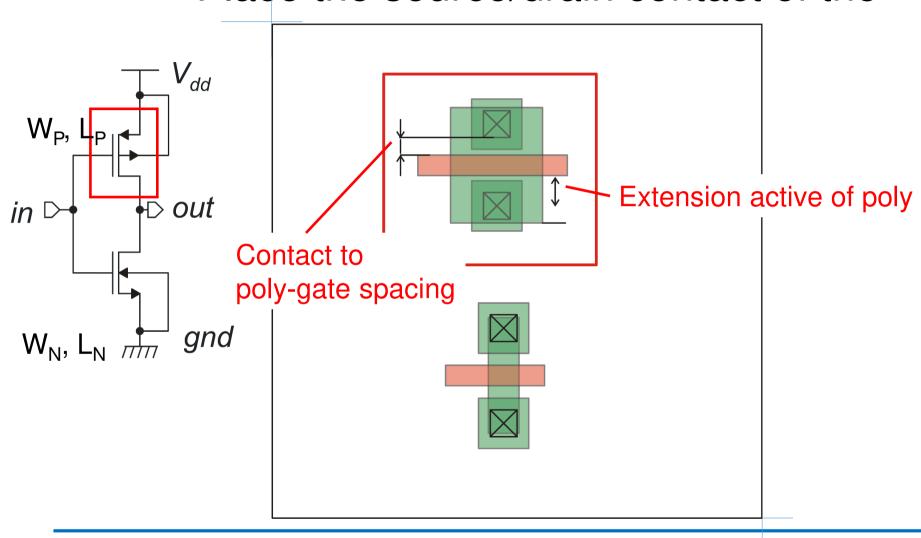
Place the n-MOS as close as possible to the n-well



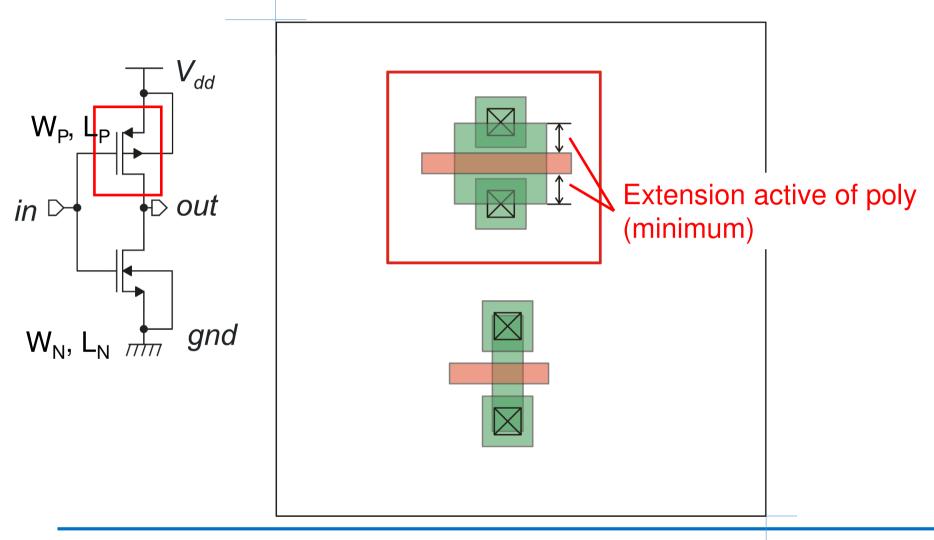
Now draw the p-MOS inside the n-well



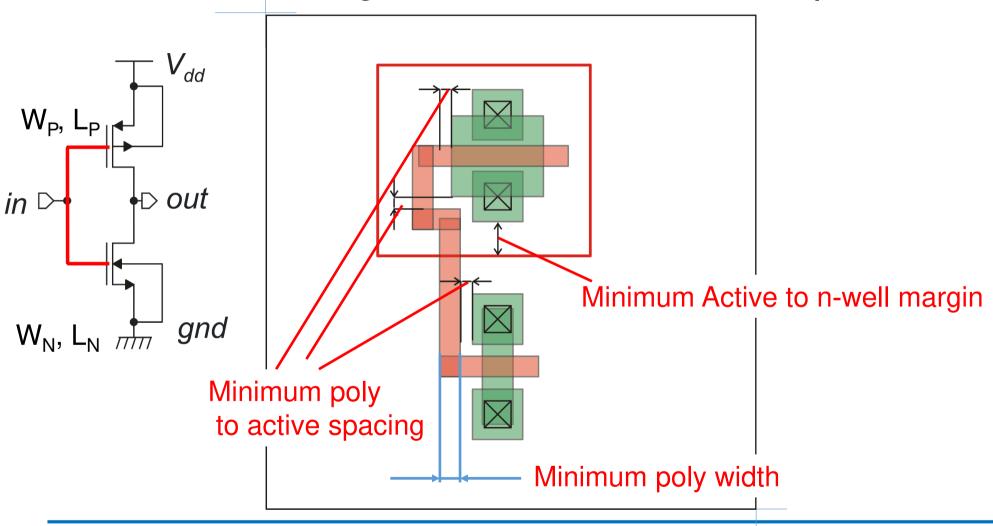
Place the source/drain contact of the



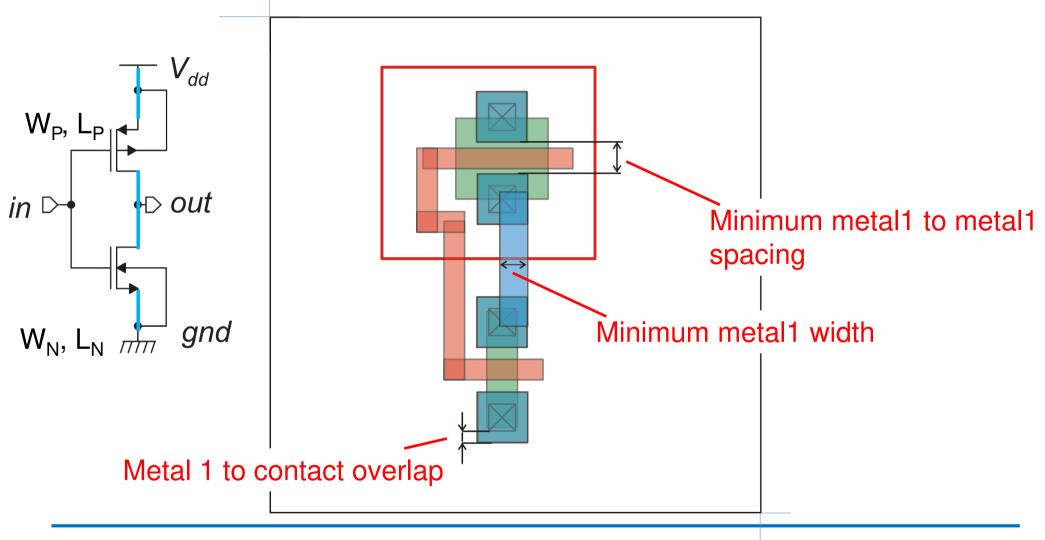
Reduce the active extension to the minimum



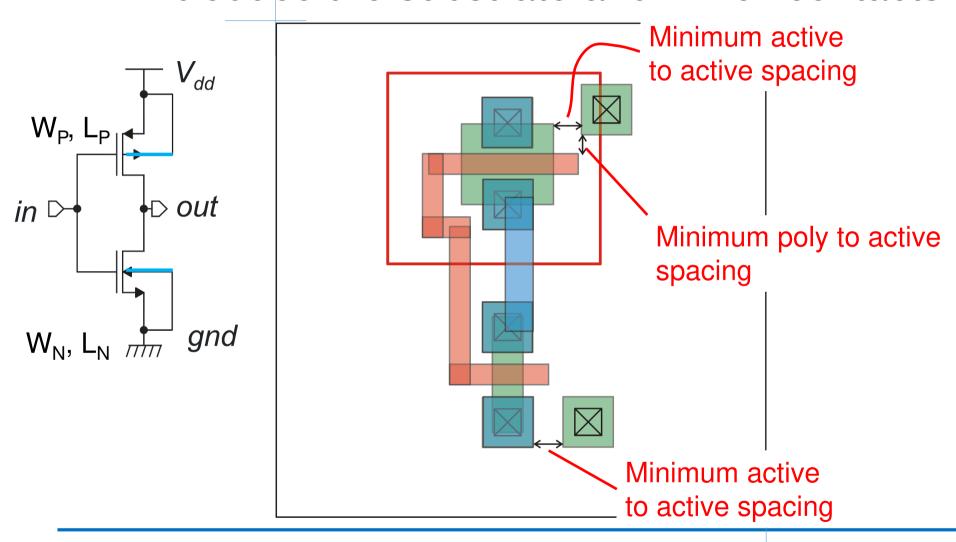
Connect the gates of the n-MOS and p-MOS



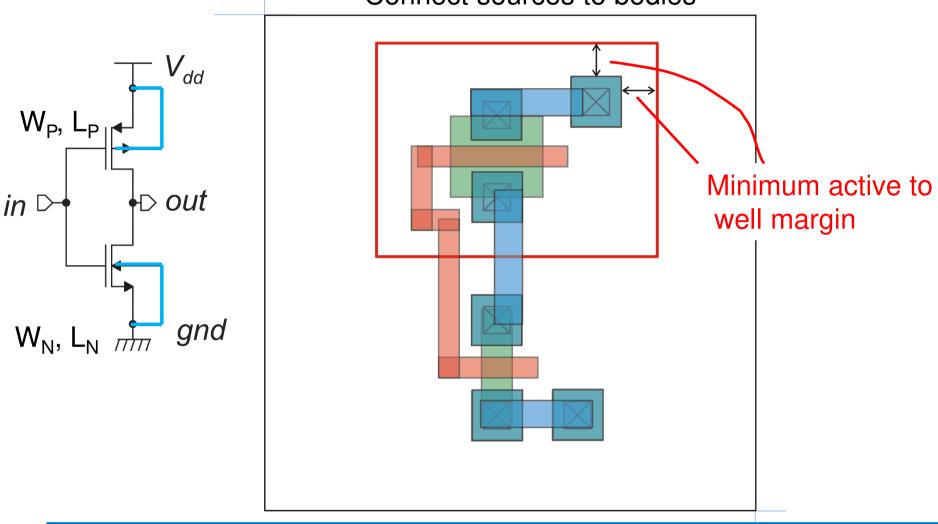
Introduce the metal-1 connections



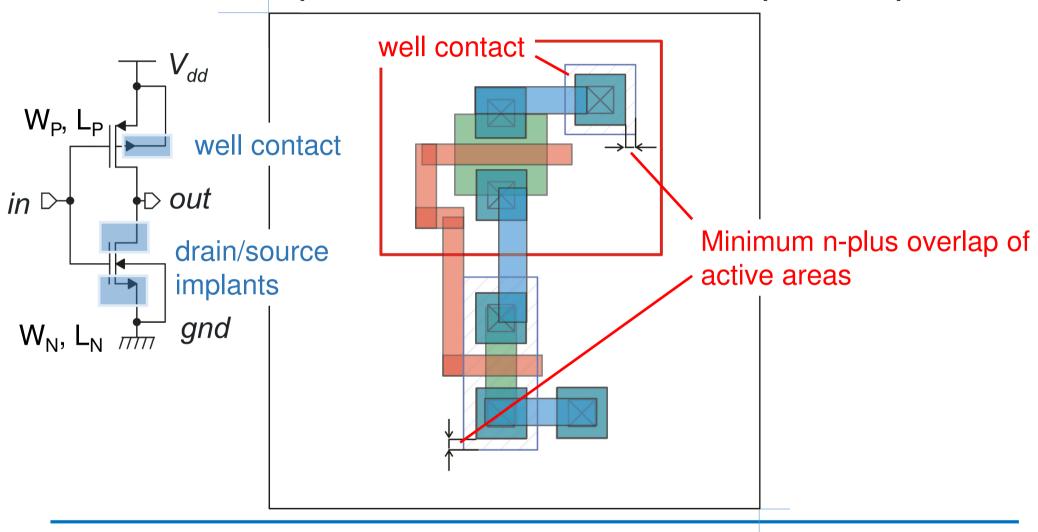
Introduce the substrate and n-well contacts



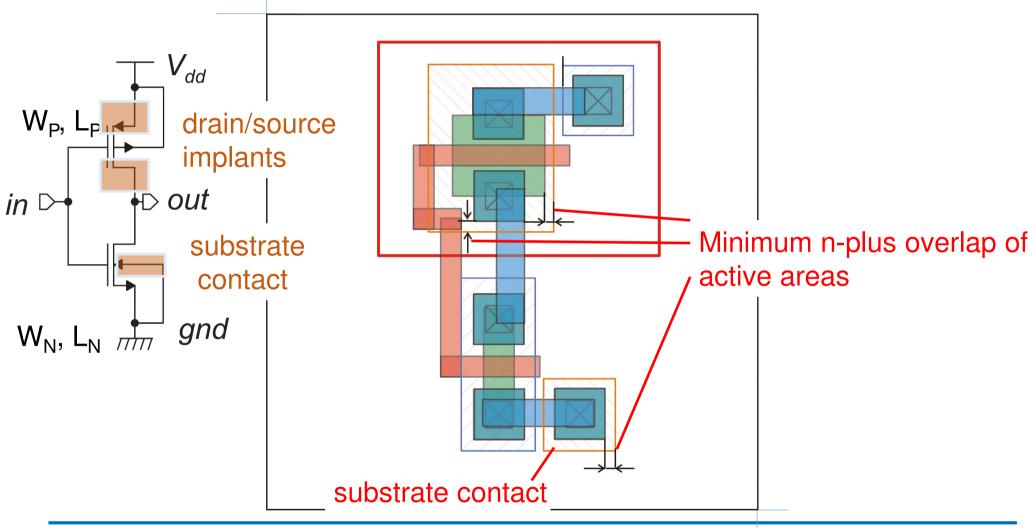
Resize the n-well to comply with all active margins. Connect sources to bodies



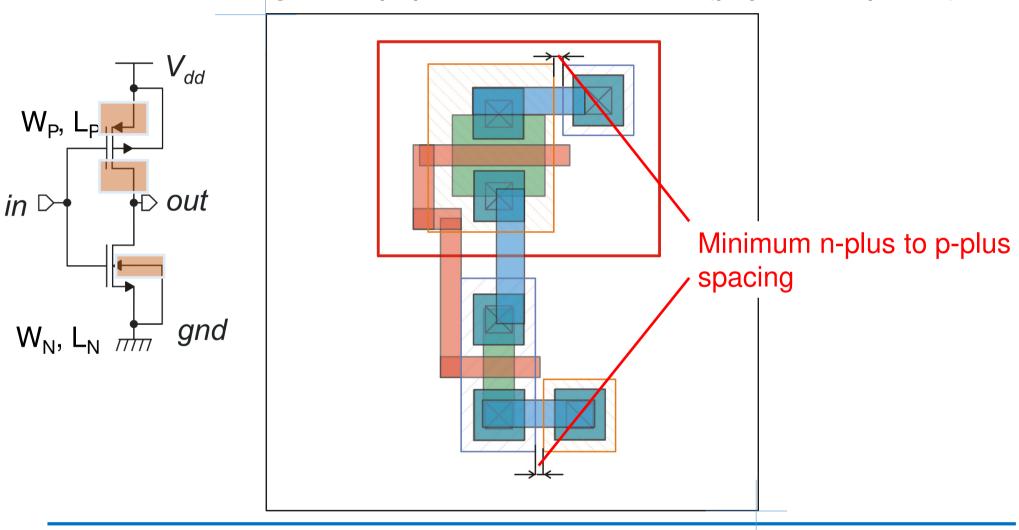
Cover all n-plus active areas with n-plus implant



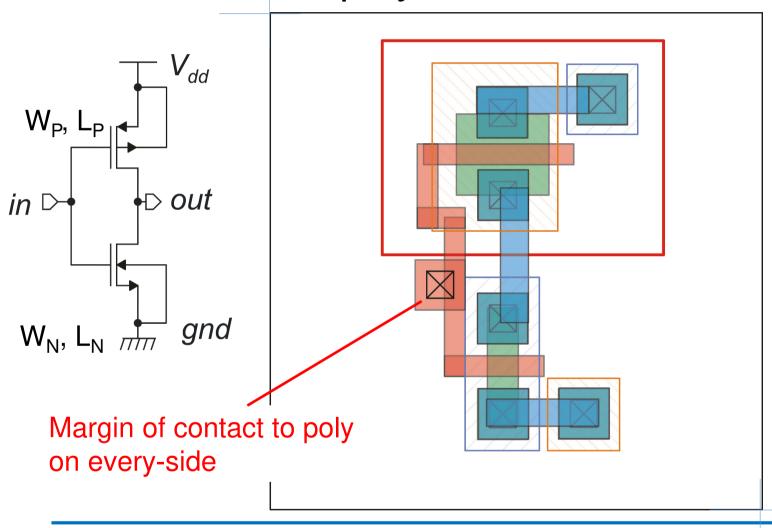
Same thing with p-plus active areas (p-plus implant)



Same thing with p-plus active areas (p-plus implant)



Create a poly-metal1 contact if required



Create a poly-metal1 contact if required

